# **Small Signal MOSFET**

20 V, 540 mA, Dual N-Channel

## Features

- Low R<sub>DS(on)</sub> Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- ESD Protected Gate
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

### Applications

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

### **MAXIMUM RATINGS** (T<sub>J</sub> = $25^{\circ}C$ unless otherwise noted.)

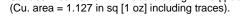
Paramet	Symbol	Value	Unit		
Drain-to-Source Voltage	V <sub>DSS</sub>	20	V		
Gate-to-Source Voltage			V <sub>GS</sub>	±7.0	V
Continuous Drain Current	Steady	$T_A = 25^{\circ}C$	1-	540	mA
(Note 1)	State	$T_A = 85^{\circ}C$	ID	390	
Power Dissipation (Note 1)	Stea	dy State	P <sub>D</sub>	250	mW
Continuous Drain Current	$t \le 5 s$ $T_A = 25^{\circ}C$		I <sub>D</sub>	570	mA
(Note 1)	1 2 3 3	$T_A = 85^{\circ}C$	טי	410	
Power Dissipation (Note 1)	t:	≤ 5 s	P <sub>D</sub>	280	mW
Pulsed Drain Current	I <sub>DM</sub>	1.5	Α		
Operating Junction and Stor	T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C		
Source Current (Body Diode)			I <sub>S</sub>	350	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			ΤL	260	°C

### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient - Steady State (Note 1)	$R_{\thetaJA}$	500	°C/W
Junction-to-Ambient – t $\leq$ 5 s (Note 1)		447	

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Surface mounted on FR4 board using 1 in sq pad size

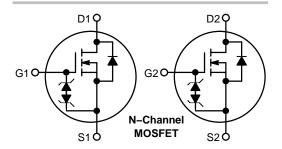


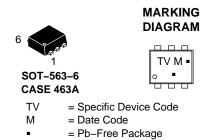


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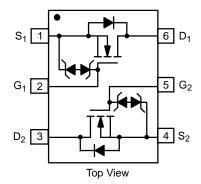
V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub> Typ	ID Max (Note 1)
20	400 mΩ @ 4.5 V	
	500 mΩ @ 2.5 V	540 mA
	700 mΩ @ 1.8 V	





(Note: Microdot may be in either location)

**PINOUT: SOT-563** 



### **ORDERING INFORMATION**

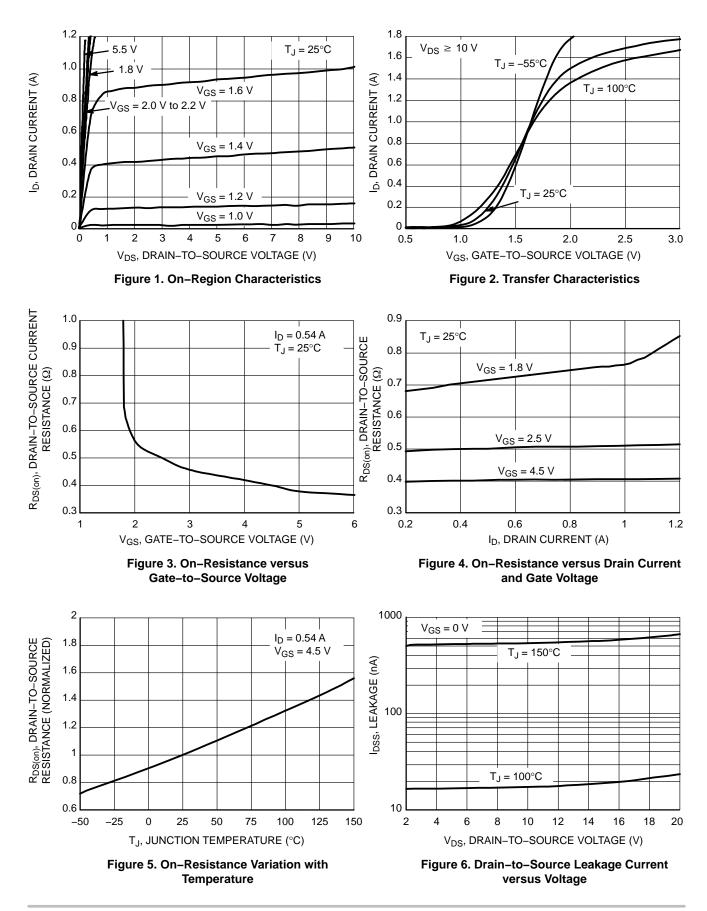
See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

## **ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> = $25^{\circ}$ C unless otherwise noted.)

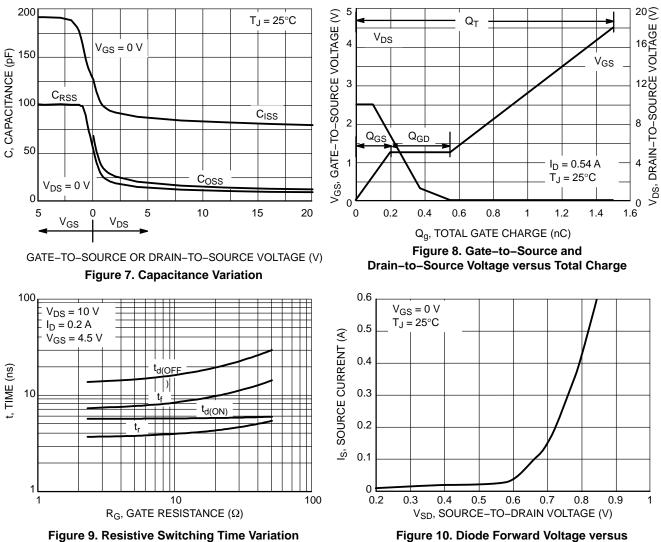
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS	-	-		-	-		·
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = 250 \text{ V}$	μΑ	20	-	-	V
Drain-to-Source Breakdown Voltage Tem- perature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	_	-		14	-	mV/°C
Zero Gate Voltage Drain Current		V <sub>GS</sub> = 0 V	$T_J = 25^{\circ}C$	-	-	1.0	μΑ
	IDSS	$V_{DS} = 16 V$	$T_J = 125^{\circ}C$	-	-	5.0	
Gate-to-Source Leakage Current	I <sub>GSS</sub>	$V_{DS}$ = 0 V, $V_{GS}$ = ±4	4.5 V	-	-	$\pm 5.0$	μΑ
ON CHARACTERISTICS (Note 3)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_{D} = 250$	) μΑ	0.45	-	1.0	V
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>	-		-	2.0	-	mV/°C
Drain-to-Source On Resistance		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 540 mA		-	0.4	0.55	Ω
	R <sub>DS(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 500	) mA	-	0.5	0.7	-
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 350	) mA	-	0.7	0.9	
Forward Transconductance	9 <sub>FS</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 540 mA			1.0	-	S
CHARGES AND CAPACITANCES	•						
Input Capacitance	C <sub>ISS</sub>				80	150	pF
Output Capacitance	C <sub>OSS</sub>	V <sub>GS</sub> = 0 V, f = 1.0 MHz, V <sub>DS</sub> = 16 V		-	13	25	
Reverse Transfer Capacitance	C <sub>RSS</sub>				10	20	
Total Gate Charge	Q <sub>G(TOT)</sub>	V <sub>GS</sub> = 4.5 V, V <sub>DS</sub> = 10 V; I <sub>D</sub> = 540 mA		-	1.5	2.5	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>			-	0.1	-	
Gate-to-Source Charge	Q <sub>GS</sub>			-	0.2	_	
Gate-to-Drain Charge	Q <sub>GD</sub>			-	0.35	_	
SWITCHING CHARACTERISTICS, $V_{GS} = V$ (	Note 4)						
Turn-On Delay Time	t <sub>d(ON)</sub>				6.0	_	ns
Rise Time	t <sub>r</sub>	$V_{GS}$ = 4.5 V, $V_{DD}$ = 10 V, $I_{D}$ = 540 mA, $R_{G}$ = 10 $\Omega$		_	4.0	-	
Turn–Off Delay Time	t <sub>d(OFF)</sub>			-	16	-	
Fall Time	t <sub>f</sub>	1			8.0	-	
DRAIN-SOURCE DIODE CHARACTERISTIC	s			•	•		<u>.                                    </u>
Forward Diode Voltage	V <sub>SD</sub>	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 350 mA	$T_J = 25^{\circ}C$	-	0.7	1.2	V
			T <sub>J</sub> = 125°C	-	0.6	-	
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V}, \text{ d}_{ISD}/\text{d}_t = 100 \text{ A}/\mu\text{s}, \text{ I}_S = 350 \text{ mA}$		_	6.5	_	ns

3. Pulse Test: pulse width  $\leq 300 \ \mu$ s, duty cycle  $\leq 2\%$ . 4. Switching characteristics are independent of operating junction temperatures.

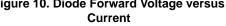
#### TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)



## **TYPICAL PERFORMANCE CURVES** ( $T_J = 25^{\circ}C$ unless otherwise noted)



versus Gate Resistance



### **ORDERING INFORMATION**

Device	Package	Shipping		
NTZD3154NT1G				
NTZD3154NT1H	SOT–563 (Pb–Free)			
NTZD3154NT2G		4000 / Tape & Reel		
NTZD3154NT2H				
NTZD3154NT5G				
NTZD3154NT5H		8000 / Tape & Reel		

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

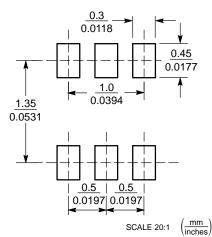
#### PACKAGE DIMENSIONS

SOT-563, 6 LEAD CASE 463A **ISSUE F** 

D -X-5 4 O 1 2 b 6 PL е  $\oplus$ 0.08 (0.003) 🔘 X | Y NOTES: NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.50	0.55	0.60	0.020	0.021	0.023	
b	0.17	0.22	0.27	0.007	0.009	0.011	
С	0.08	0.12	0.18	0.003	0.005	0.007	
D	1.50	1.60	1.70	0.059	0.062	0.066	
E	1.10	1.20	1.30	0.043	0.047	0.051	
е	0.5 BSC			0.02 BSC			
L	0.10	0.20	0.30	0.004	0.008	0.012	
HE	1.50	1.60	1.70	0.059	0.062	0.066	

#### SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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